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Kind regards,

Team Nexperia

74HC151-Q100; 74HCT151-Q100

8-input multiplexer

Rev. 3 — 26 January 2015

Product data sheet

1. General description

The 74HC151-Q100; 74HCT151-Q100 are 8-bit multiplexer with eight binary inputs (I0 to I7), three select inputs (S0 to S2) and an enable input ($\overline{E}$). One of the eight binary inputs is selected by the select inputs and routed to the complementary outputs (Y and $\overline{Y}$). A HIGH on $\overline{E}$ forces the output Y LOW and output $\overline{Y}$ HIGH. Inputs also include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Specified in compliance with JEDEC standard no. 7A
- Input levels:
 - ◆ For 74HC151-Q100: CMOS level
 - ◆ For 74HCT151-Q100: TTL level
- Low-power dissipation
- Non-inverting data path
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)
- Multiple package options

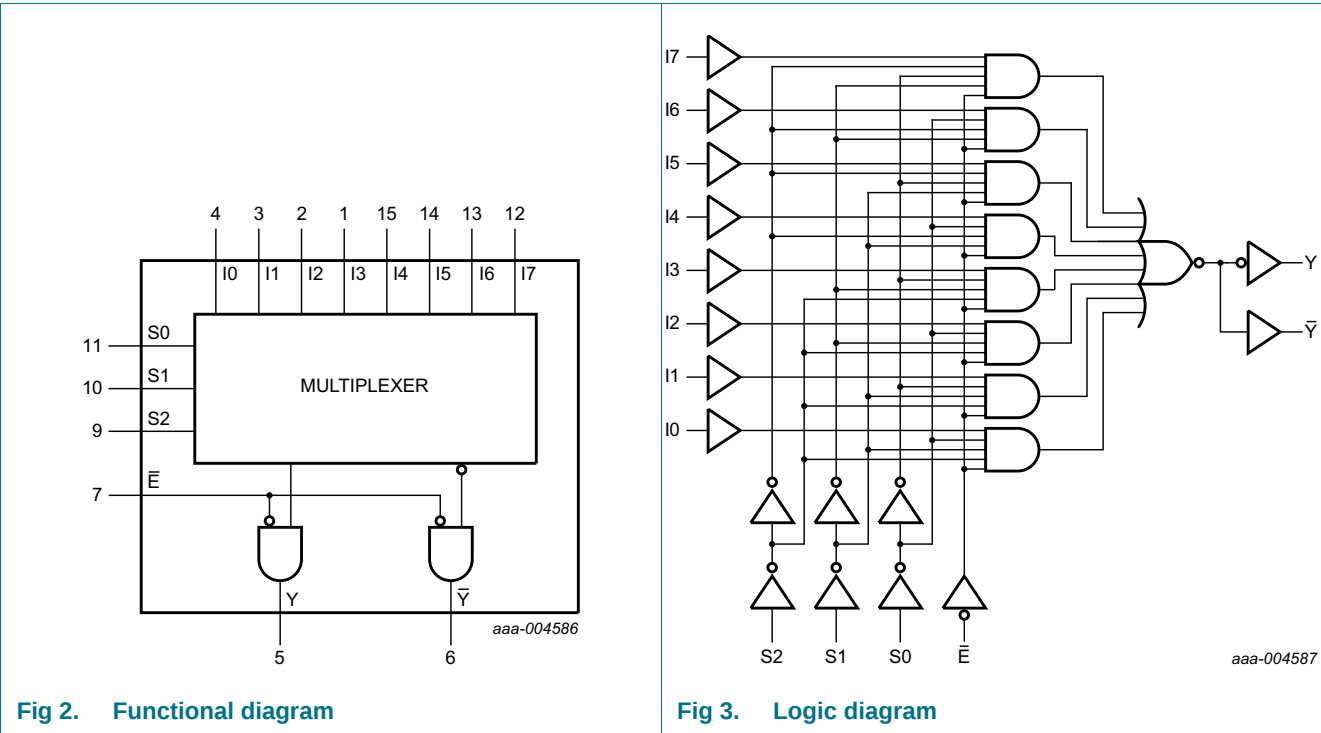
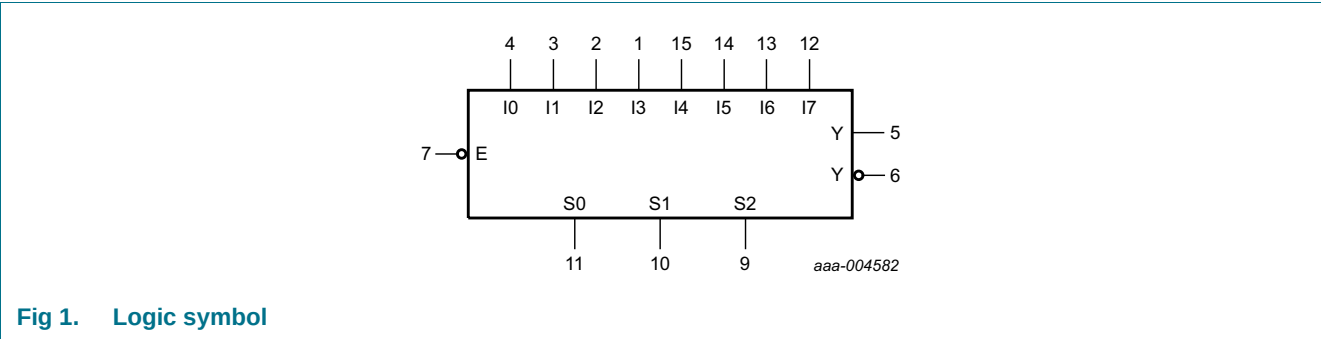
3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC151D-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT151D-Q100				
74HC151PW-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT151PW-Q100				

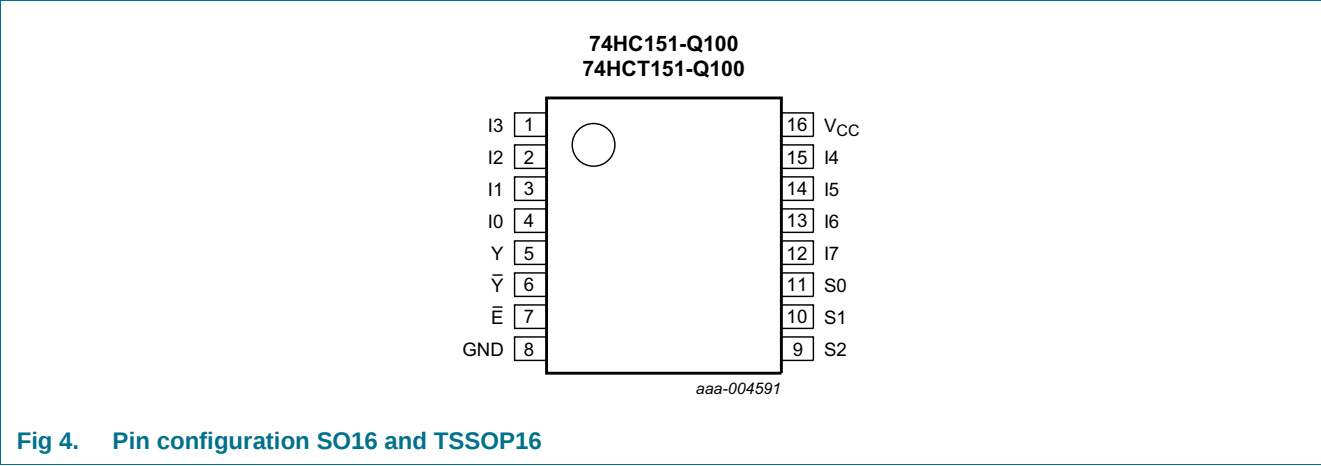


4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
I0 to I7	4, 3, 2, 1, 15, 14, 13, 12	data inputs
Y	5	multiplexer output
$\bar{Y}$	6	complementary multiplexer output
$\bar{E}$	7	enable input (active LOW)
GND	8	ground (0 V)
S0, S1, S2	11, 10, 9	common data select inputs
V _{CC}	16	supply voltage

6. Functional description

Table 3. Function table^[1]

Input												Output	
$\overline{E}$	S2	S1	S0	I0	I1	I2	I3	I4	I5	I6	I7	$\overline{Y}$	Y
H	X	X	X	X	X	X	X	X	X	X	X	H	L
L	L	L	L	L	X	X	X	X	X	X	X	H	L
L	L	L	L	H	X	X	X	X	X	X	X	L	H
L	L	L	H	X	L	X	X	X	X	X	X	H	L
L	L	L	H	X	H	X	X	X	X	X	X	L	H
L	L	H	L	X	X	L	X	X	X	X	X	H	L
L	L	H	L	X	X	H	X	X	X	X	X	L	H
L	L	H	H	X	X	X	L	X	X	X	X	H	L
L	L	H	H	X	X	X	H	X	X	X	X	L	H
L	H	L	L	X	X	X	X	L	X	X	X	H	L
L	H	L	L	X	X	X	X	H	X	X	X	L	H
L	H	L	H	X	X	X	X	X	L	X	X	H	L
L	H	L	H	X	X	X	X	X	H	X	X	L	H
L	H	H	L	X	X	X	X	X	X	L	X	H	L
L	H	H	L	X	X	X	X	X	X	H	X	L	H
L	H	H	H	X	X	X	X	X	X	X	L	H	L
L	H	H	H	X	X	X	X	X	X	X	H	L	H

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_O	output current	$V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$	-	± 25	mA
I_{CC}	supply current		-	+50	mA
I_{GND}	ground current		-	-50	mA
T_{stg}	storage temperature		-65	+150	°C

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C			
	SO16 package	[1]	-	500	mW
	TSSOP16 package	[2]	-	500	mW

[1] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

[2] For TSSOP16 package: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC151-Q100			74HCT151-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = –40 °C to +85 °C		T _{amb} = –40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC151-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = –20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = –20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = –4.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I _O = –5.2 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
C _I	input capacitance		-	3.5	-					pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = –40 °C to +85 °C		T _{amb} = –40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT151-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = –20 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –4 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	-	80	-	160	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} – 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A								
		per input pin; In inputs	-	45	162	-	203	-	221	µA
		per input pin; $\overline{E}$ input	-	30	108	-	135	-	147	µA
		per input pin; Sn input	-	150	540	-	675	-	735	µA
C _I	input capacitance		-	3.5	-					pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = −40 °C to +85 °C		T _{amb} = −40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC151-Q100										
t _{pd}	propagation delay	In to Y; see Figure 5 ^[1]								
		V _{CC} = 2.0 V	-	52	170	-	215	-	255	ns
		V _{CC} = 4.5 V	-	19	34	-	43	-	51	ns
		V _{CC} = 5 V; C _L = 15 pF	-	17	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	15	29	-	37	-	43	ns
		In to $\overline{Y}$; see Figure 5 ^[1]								
		V _{CC} = 2.0 V	-	58	185	-	230	-	280	ns
		V _{CC} = 4.5 V	-	21	37	-	46	-	56	ns
		V _{CC} = 5 V; C _L = 15 pF	-	17	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	17	31	-	39	-	48	ns
		Sn to Y; see Figure 6 ^[1]								
		V _{CC} = 2.0 V	-	61	185	-	230	-	280	ns
		V _{CC} = 4.5 V	-	22	37	-	46	-	56	ns
		V _{CC} = 5 V; C _L = 15 pF	-	19	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	18	31	-	39	-	48	ns
		Sn to $\overline{Y}$; see Figure 6 ^[1]								
		V _{CC} = 2.0 V	-	61	205	-	255	-	310	ns
		V _{CC} = 4.5 V	-	22	41	-	51	-	62	ns
		V _{CC} = 5 V; C _L = 15 pF	-	19	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	18	35	-	43	-	53	ns
		$\overline{E}$ to Y; see Figure 6								
		V _{CC} = 2.0 V	-	41	125	-	155	-	190	ns
		V _{CC} = 4.5 V	-	15	25	-	31	-	38	ns
		V _{CC} = 5 V; C _L = 15 pF	-	12	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	12	21	-	26	-	32	ns
		$\overline{E}$ to $\overline{Y}$; see Figure 6								
		V _{CC} = 2.0 V	-	47	145	-	180	-	220	ns
		V _{CC} = 4.5 V	-	17	29	-	36	-	44	ns
		V _{CC} = 5 V; C _L = 15 pF	-	14	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	25	-	31	-	38	ns
t _t	transition time	Y, $\overline{Y}$; see Figure 5 ^[2]								
		V _{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V	-	6	13	-	16	-	19	ns

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	$T_{amb} = 25\text{ }^{\circ}\text{C}$			$T_{amb} = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$		$T_{amb} = -40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C_{PD}	power dissipation capacitance	$C_L = 50$ pF; $f = 1$ MHz; $V_I = \text{GND to } V_{CC}$ [3]	-	40	-	-	-	-	-	pF
74HCT151-Q100										
t_{pd}	propagation delay	In to Y; see Figure 5 [1]								
		$V_{CC} = 4.5$ V	-	22	38	-	48	-	57	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	19	-	-	-	-	-	ns
		In to $\bar{Y}$; see Figure 5 [1]								
		$V_{CC} = 4.5$ V	-	22	38	-	48	-	57	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	19	-	-	-	-	-	ns
		Sn to Y; see Figure 6 [1]								
		$V_{CC} = 4.5$ V	-	23	41	-	51	-	62	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	20	-	-	-	-	-	ns
		Sn to $\bar{Y}$; see Figure 6 [1]								
		$V_{CC} = 4.5$ V	-	25	43	-	54	-	65	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	20	-	-	-	-	-	ns
		$\bar{E}$ to Y; see Figure 6 [1]								
		$V_{CC} = 4.5$ V	-	16	29	-	36	-	44	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	13	-	-	-	-	-	ns
		$\bar{E}$ to $\bar{Y}$; see Figure 6 [1]								
		$V_{CC} = 4.5$ V	-	21	36	-	45	-	54	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	18	-	-	-	-	-	ns
t_t	transition time	Y, $\bar{Y}$; see Figure 5 [2]								
		$V_{CC} = 4.5$ V	-	7	15	-	19	-	22	ns
C_{PD}	power dissipation capacitance	$C_L = 50$ pF; $f = 1$ MHz; $V_I = \text{GND to } V_{CC} - 1.5$ V [3]	-	40	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] t_t is the same as t_{THL} and t_{TLH} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms

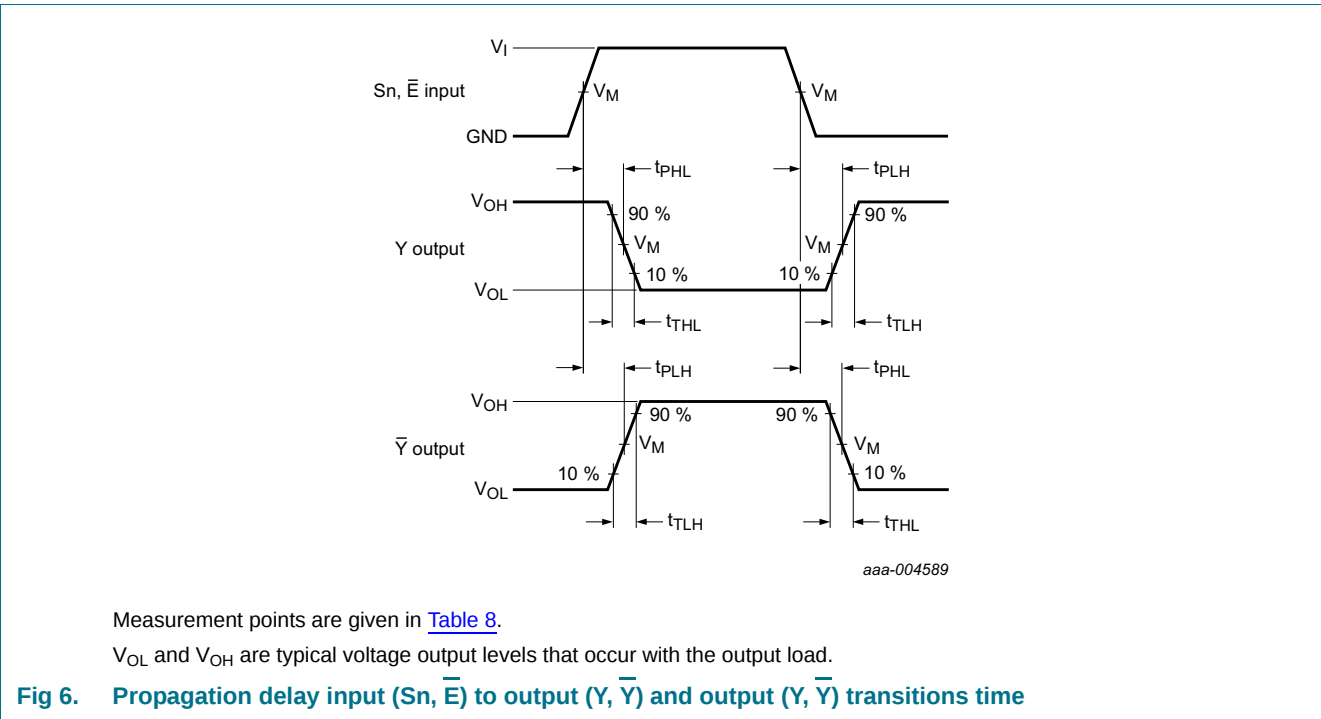
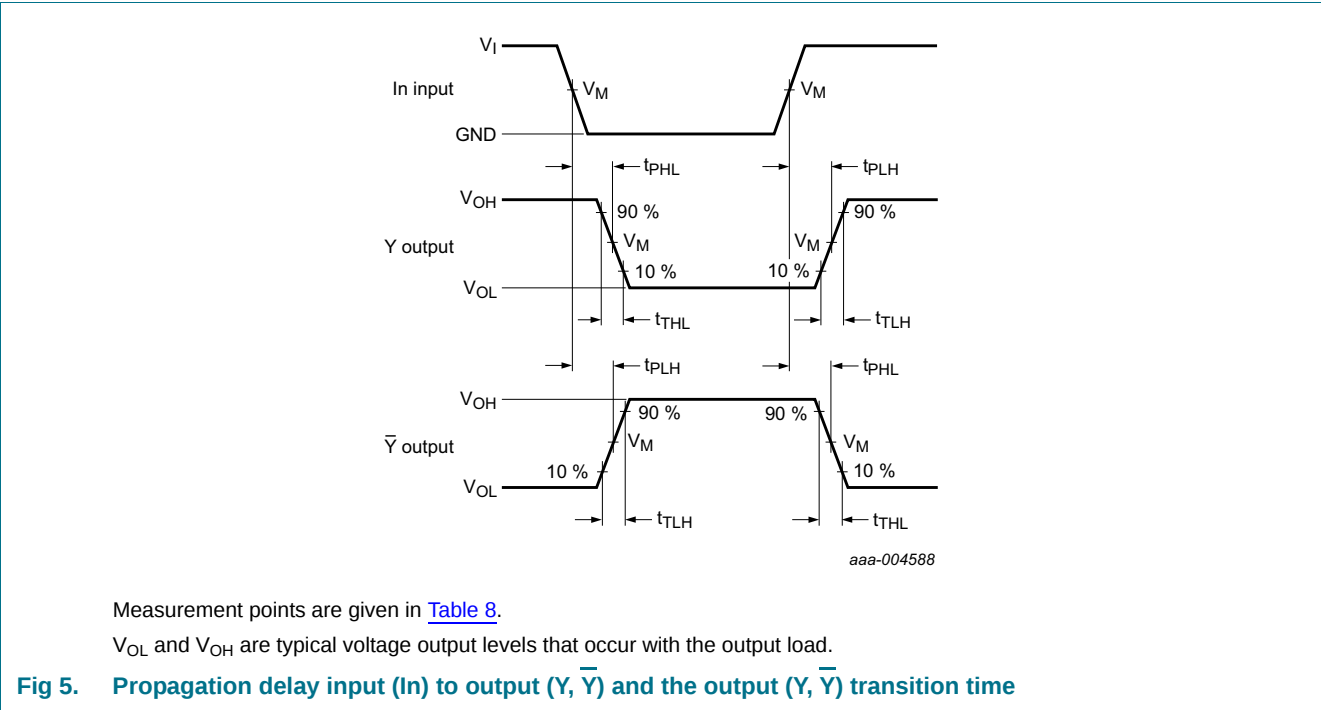
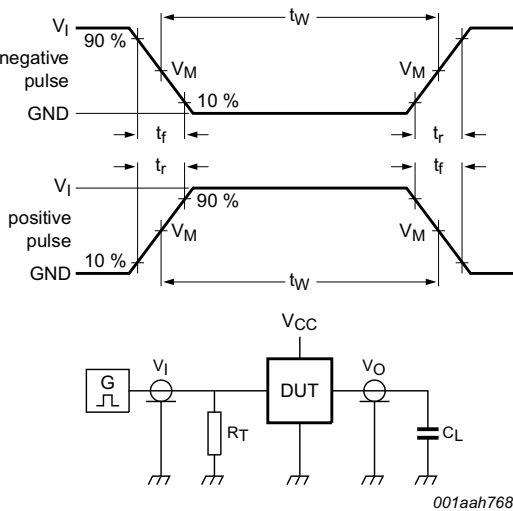


Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74HC151-Q100	$0.5V_{CC}$	$0.5V_{CC}$
74HCT151-Q100	1.3 V	1.3 V



Test data is given in [Table 9](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 7. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load	Test
	V_I	t_r, t_f	C_L	
74HC151-Q100	V_{CC}	6.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}
74HCT151-Q100	3.0 V	6.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

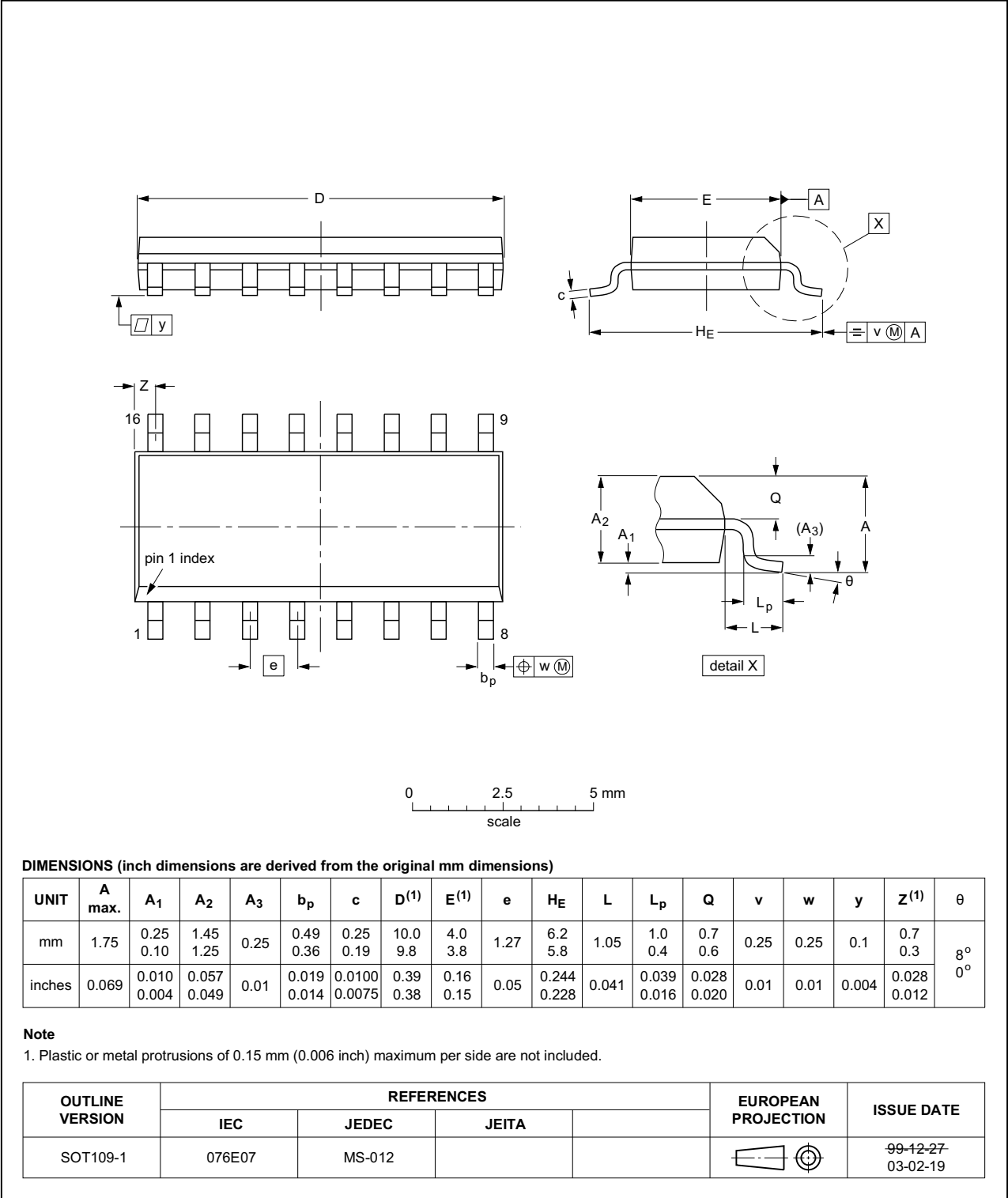
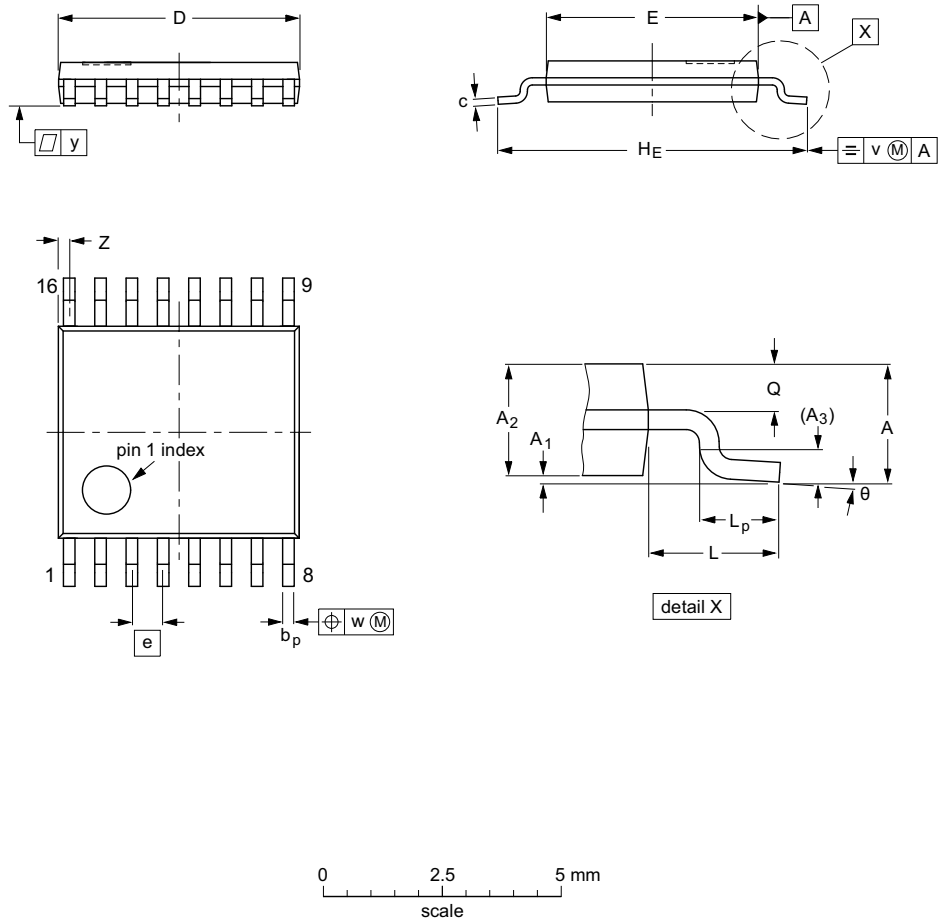


Fig 8. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

- Notes**
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				-99-12-27- 03-02-18

Fig 9. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT151_Q100 v.3	20150126	Product data sheet	-	74HC_HCT151_Q100 v.2
Modifications:	• Table 7 : Power dissipation capacitance condition for 74HCT151-Q100 is corrected.			
74HC_HCT151_Q100 v.2	20130211	Product data sheet	-	74HC_HCT151_Q100 v.1
Modifications:	• New descriptive title (errata).			
74HC_HCT151_Q100 v.1	20120807	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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